



STD1NC40-1

N - CHANNEL 400V - 8Ω - 1A - IPAK PowerMESH™ II MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STD1NC40-1	400 V	< 10 Ω	1 A

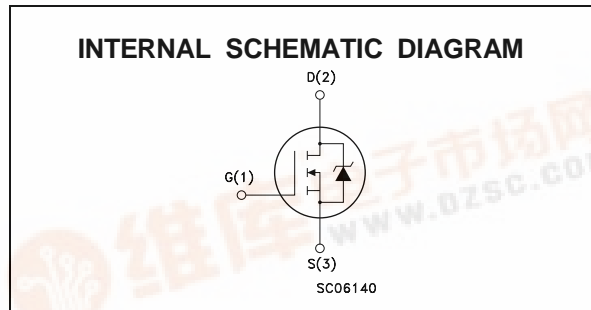
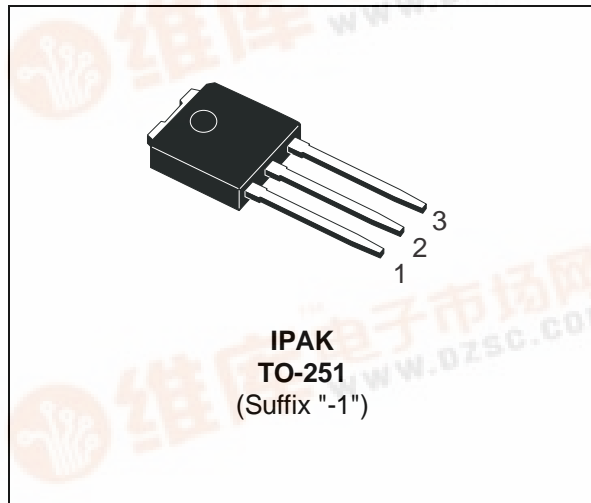
- TYPICAL R_{DS(on)} = 8 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

DESCRIPTION

Using the latest high voltage MESH OVERLAY™ II process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R_{DS(on)} per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

APPLICATIONS

- SWITCH MODE LOW POWER SUPPLIES (SMPS)
- CFL



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	400	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	400	V
V _{GS}	Gate-source Voltage	± 30	V
I _D	Drain Current (continuous) at T _c = 25 °C	1	A
I _D	Drain Current (continuous) at T _c = 100 °C	0.63	A
I _{DM} (•)	Drain Current (pulsed)	4	A
P _{tot}	Total Dissipation at T _c = 25 °C	25	W
	Derating Factor	0.2	W/°C
dv/dt	Peak Diode Recovery voltage slope	3	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 1A, di/dt ≤ 100 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}



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THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	5	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	100	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	1.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		275	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	1	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	20	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	400			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 30 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 0.5 A		8	10	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	1			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 1 A		0.4		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		100		pF
C _{oss}	Output Capacitance			25		pF
C _{rss}	Reverse Transfer Capacitance			2		pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 200\text{ V}$ $I_D = 0.5\text{ A}$		12		ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		21		ns
Q_g	Total Gate Charge	$V_{DD} = 320\text{ V}$ $I_D = 1\text{ A}$ $V_{GS} = 10\text{ V}$		4		nC
Q_{gs}	Gate-Source Charge			2		nC
Q_{gd}	Gate-Drain Charge			2.5		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(voff)}$	Off-voltage Rise Time	$V_{DD} = 320\text{ V}$ $I_D = 1\text{ A}$		11		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		21		ns
t_c	Cross-over Time			10		ns

SOURCE DRAIN DIODE

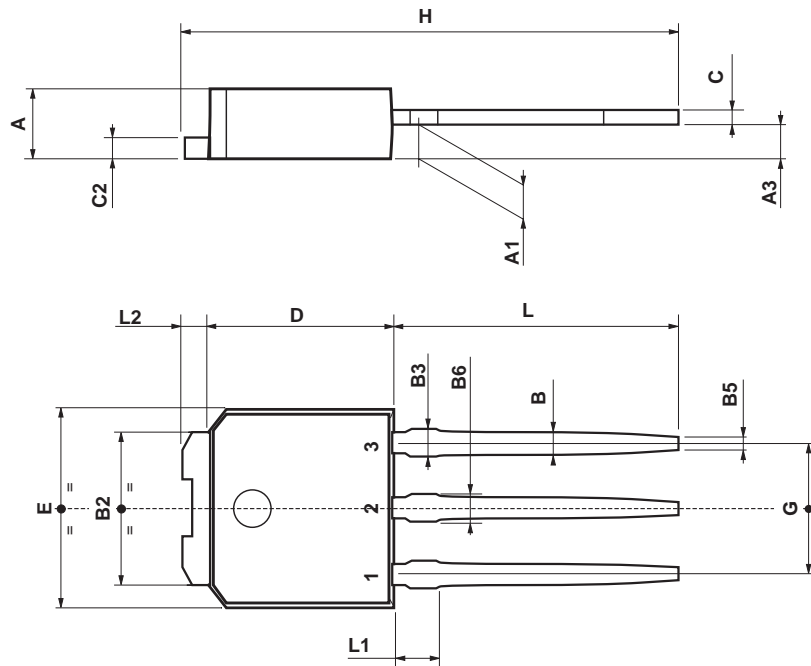
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				1	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				4	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 1\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 1\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		340		ns
Q_{rr}	Reverse Recovery Charge			0.95		μC
I_{RRM}	Reverse Recovery Current			5.6		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



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